

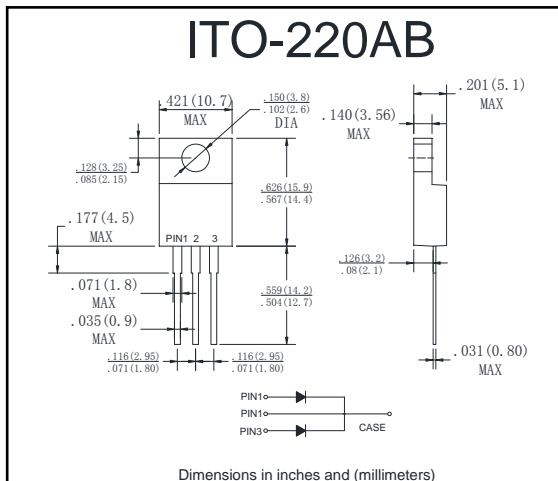


肖特基二极管 SCHOTTKY Diodes

■ 特征 Features

- 耐正向浪涌电流能力高
High surge forward current capability
- 低功耗，大电流
Low Power loss, High efficiency
- I_o 15.0A
- V_{RRM} 40-200V

■ 外形尺寸和印记 Outline Dimensions and Mark



■ 用途 Applications

- 快速整流用
High speed switching

■ 极限值（绝对最大额定值）

Limiting Values (Absolute Maximum Rating)

参数名称 Item	符号 Symbol	单位 Unit	条件 Conditions	MBR15-FCT					
				40	60	80	100	150	200
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V		40	60	80	100	150	200
平均整流输出电流 Average Rectified Output Current	I_o	A	正弦半波 60Hz, 电阻负载, T_a (Fig.1) 60HZ Half-sine wave, Resistance load, T_a (Fig.1)	15					
正向(不重复)浪涌电流 Surge(Non-repetitive)Forward Current	I_{FSM}	A	60HZ正弦波, 一个周期, $T_a=25^\circ C$ 60HZ sine wave, 1 cycle, $T_a=25^\circ C$	100					
正向浪涌电流的平方对电流浪涌持续时间的积分值 Current Squared Time	I^2t	A^2s	$1ms \leq t < 8.3ms$ $T_j=25^\circ C$, 单个二极管 $1ms \leq t < 8.3ms$ $T_j=25^\circ C$, Rating of per diode	41					
贮存温度 Storage Temperature	T_{stg}	°C		-55 ~ +150					
结温 Junction Temperature	T_j	°C	在正向直流条件下, 没有施加反向压降, 通电≤1 h (图示1) ① IN DC Forward Mode-Forward Operations, without reverse bias, $t \leq 1 h$ (Fig. 1)①	-55 ~ +150					

■ 电特性 ($T_a=25^\circ C$ 除非另有规定)Electrical Characteristics ($T_a=25^\circ C$ Unless otherwise specified)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition	MBR15-FCT					
				40	60	80	100	150	200
正向峰值电压 Peak Forward Voltage	V_{FM}	V	$I_{FM} = 7.5A$	0.55	0.75	0.85	0.90	0.95	
反向峰值电流 Peak Reverse Current	I_{RRM1}	mA	$V_{RM} = V_{RRM}$	$T_a=25^\circ C$	0.1				
	I_{RRM2}			$T_a=100^\circ C$	20				
热阻 Thermal Resistance	$R_{\theta J-C}$	°C/W	结和壳之间 Between junction and case	2.0					

■ 备注 NOTE

① Meets the requirements of IEC 61215 Ed. 2 bypass diode thermal test.



■ 特性曲线(典型) Characteristics(Typical)

图1: 正向电流降额曲线

FIG1: IF (AV) --Tc Derating

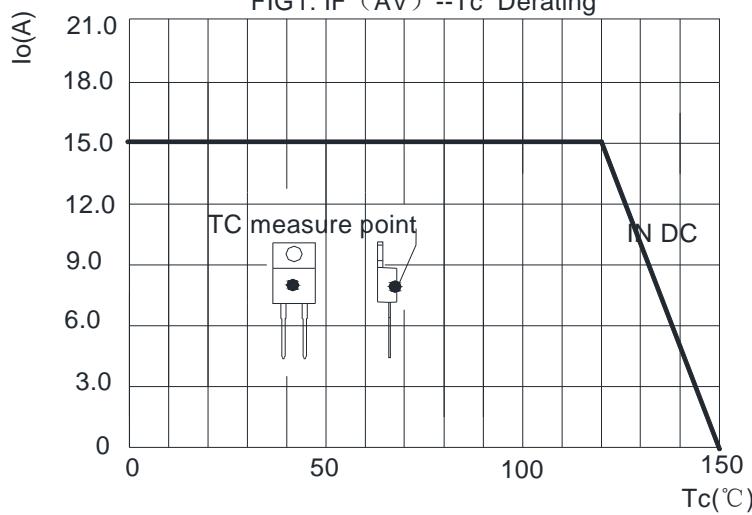


图2: 耐正向浪涌电流曲线

FIG2: Surge Forward Current Capability

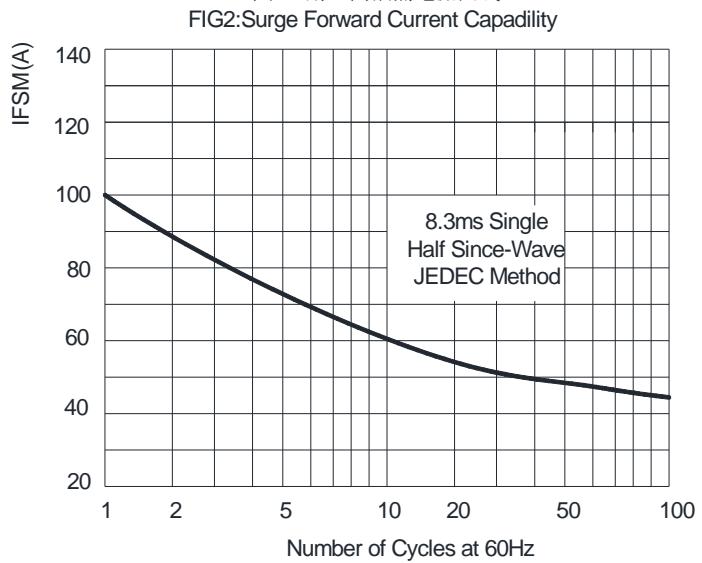


图3: 正向电压曲线

FIG3: Instantaneous Forward Voltage

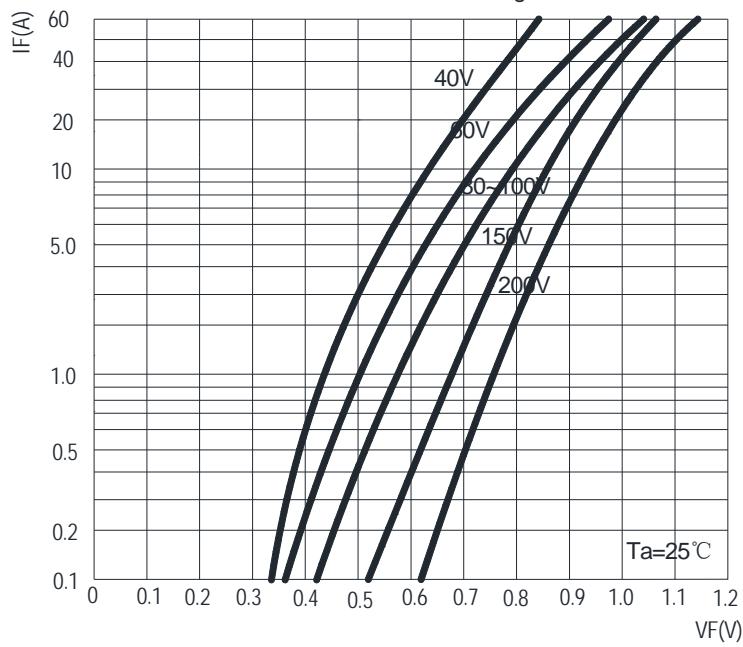


图4: 反向电流曲线

FIG4: Typical Reverse Characteristics

